Product data sheet

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NXP Semiconductors





FEATURES

- High voltage, current controlled
- RF resistor for RF attenuators and switches
- Low diode capacitance
- Low diode forward resistance
- · Very low series inductance
- For applications up to 3 GHz.

APPLICATIONS

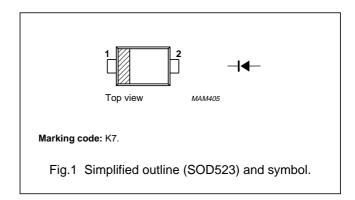
• RF attenuators and switches.

DESCRIPTION

Planar PIN diode in a SOD523 ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION		
1	cathode		
2	anode		



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	60	V
I _F	continuous forward current		_	100	mA
P _{tot}	total power dissipation	T _s ≤ 90 °C	_	715	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-65	+150	°C

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS		MAX.	UNIT
V _F	forward voltage	I _F = 50 mA	0.95	1.1	V
I _R	reverse leakage current	V _R = 60 V	_	100	nA
C _d diode capacitance		V _R = 0; f = 1 MHz	0.4	_	pF
		V _R = 1 V; f = 1 MHz	0.35	0.45	pF
		V _R = 20 V; f = 1 MHz	0.25	0.32	pF
r _D	diode forward resistance	f = 100 MHz; note 1			
		$I_{F} = 0.5 \text{ mA}$	3.4	5.0	Ω
		$I_F = 1 \text{ mA}$	2.4	3.6	Ω
		I _F = 10 mA	1.2	1.8	Ω
		$I_{F} = 100 \text{ mA}$	0.85	1.3	Ω
s ₂₁ ²	isolation	V _R = 0; f = 900 MHz	16.3	_	dB
		V _R = 0; f = 1800 MHz	11.4	_	dB
		V _R = 0; f = 2450 MHz	9.2	_	dB
s ₂₁ ² insertion loss	insertion loss	I _F = 0.5 mA; f = 900 MHz	0.23	_	dB
		I _F = 0.5 mA; f = 1800 MHz	0.27	_	dB
		I _F = 0.5 mA; f = 2450 MHz	0.33	_	dB
s ₂₁ ²	insertion loss	I _F = 1 mA; f = 900 MHz	0.18	_	dB
		I _F = 1 mA; f = 1800 MHz	0.22	_	dB
		I _F = 1 mA; f = 2450 MHz	0.27	_	dB
s ₂₁ ²	insertion loss	I _F = 10 mA; f = 900 MHz	0.10	_	dB
		I _F = 10 mA; f = 1800 MHz	0.16	_	dB
		I _F = 10 mA; f = 2450 MHz	0.20	_	dB
S ₂₁ ²	insertion loss	I _F = 100 mA; f = 900 MHz	0.08	_	dB
		I _F = 100 mA; f = 1800 MHz	0.13	_	dB
		I _F = 100 mA; f = 2450 MHz	0.18	_	dB
τ∟	charge carrier life time	when switched from $I_F = 10$ mA to $I_R = 6$ mA; $R_L = 100 \Omega$; measured at $I_R = 3$ mA		_	μs
L _S	series inductance	$I_F = 100 \text{ M}$; f = 100 MHz		_	nH

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point		K/W

^{1.} Guaranteed on AQL basis: inspection level S4, AQL 1.0.

GRAPHICAL DATA

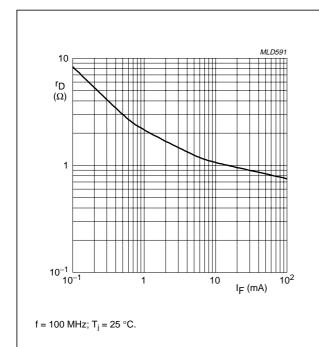


Fig.2 Forward resistance as a function of forward current; typical values.

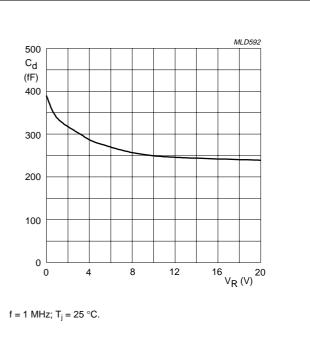
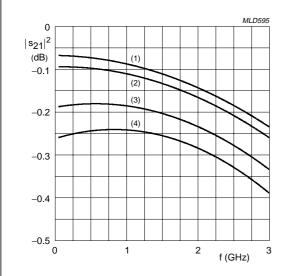


Fig.3 Diode capacitance as a function of reverse voltage; typical values.

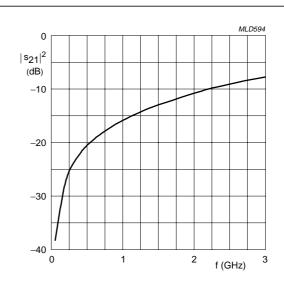


- (1) $I_F = 100 \text{ mA}.$
- (3) $I_F = 1 \text{ mA}.$
- (2) $I_F = 10 \text{ mA}.$
- (4) $I_F = 0.5 \text{ mA}.$

Diode inserted in series with a 50 Ω stripline circuit and biased via the analyzer Tee network.

 $T_{amb} = 25 \, ^{\circ}C.$

Fig.4 Insertion loss $(|s_{21}|^2)$ of the diode as a function of frequency; typical values.



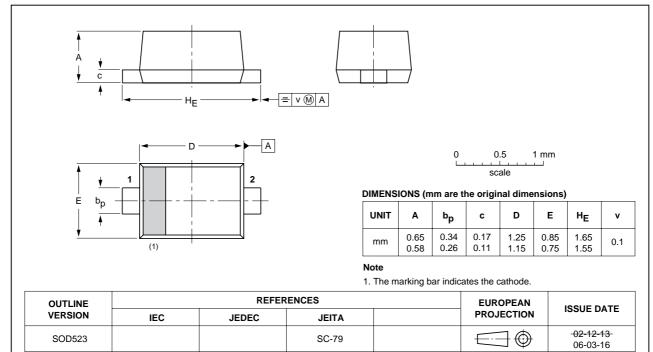
Diode zero biased and inserted in series with a 50 Ω stripline circuit. T_{amb} = 25 $^{\circ}C.$

Fig.5 Isolation ($|s_{21}|^2$) of the diode as a function of frequency; typical values.

PACKAGE OUTLINE

Plastic surface-mounted package; 2 leads

SOD523



Silicon PIN diode

Legal information

Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Silicon PIN diode

Revision history

Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BAP1321-02_N_2	20080103	Product data sheet	-	BAP1321-02_1	
Modifications: • Package outline drawing on page 5 changed					
BAP1321-02_1 (9397 750 08131)	20010417	Product specification	-	-	

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Document identifier: BAP1321-02_N_2